

Supporting Information

Polystyrene-Block-Poly (methacrylate) Composite Materials Film as a Gate Dielectric for Plastic Thin-Film Transistor Applications

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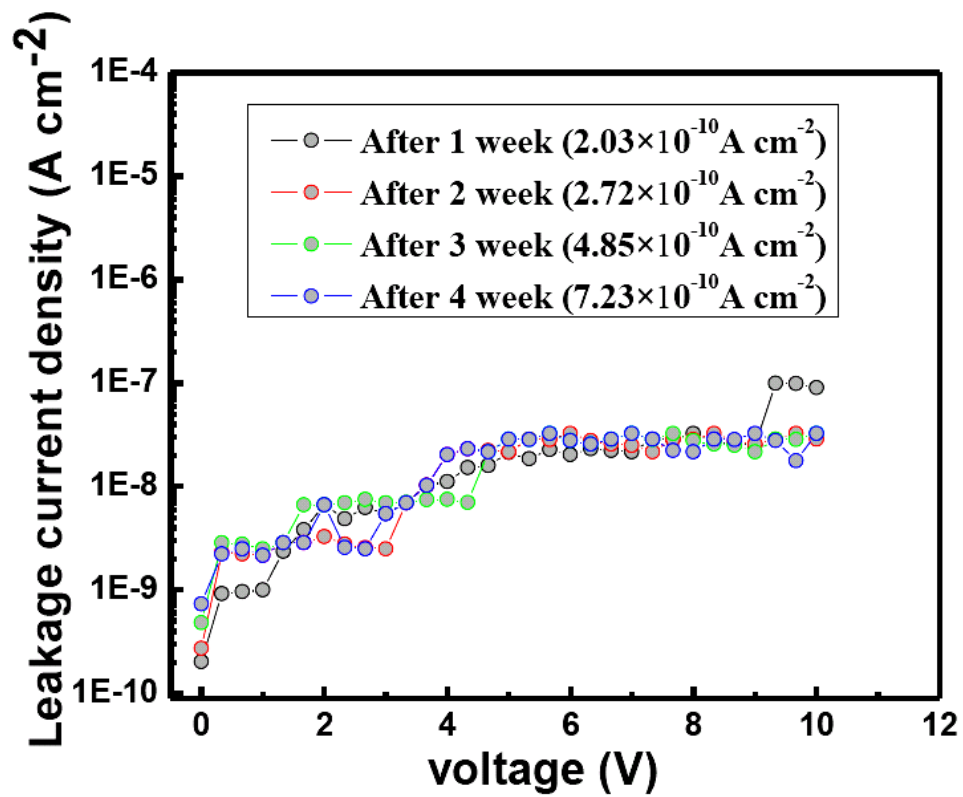


Figure S1. Leakage current density measurements test for 1 day to 4 weeks for double layer PS-*b*-PMMA film (28 nm thick) as dielectric layer in MIM structured device.

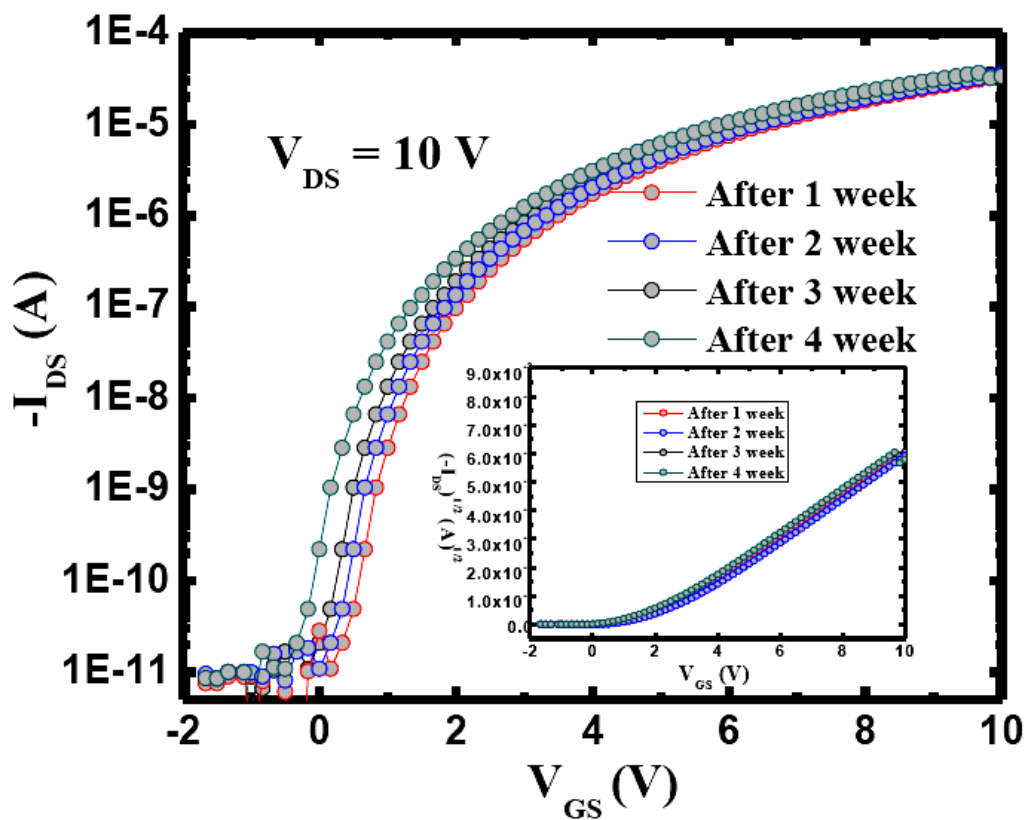


Figure S2. Transfer characteristic ($I_{DS}-V_{GS}$), when $V_{DS}=10$ V for double layer PS-*b*-PMMA film (28 nm thick) as gate dielectric layer and ZnO as semiconductor active layer for day 1 to 4 weeks.